Stanford



John Bravman

Bing Centennial Prof, Freeman-Thornton Chair for Vice Provost for Undergrad Ed, & Dean of Fresh-Soph College, & Prof of Materials Sci & Eng, Emeritus

Materials Science and Engineering

Bio

BIO

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ACADEMIC APPOINTMENTS

- Emeritus Faculty, Acad Council, Materials Science and Engineering
- Member, Cardiovascular Institute

ADMINISTRATIVE APPOINTMENTS

- President, Bucknell University, (2010- present)

Publications

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- **Stress relaxation in free-standing aluminum beams** *THIN SOLID FILMS*
  Lee, H. J., Zhang, P., Bravman, J. C.
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- **Stress-induced and electromigration voiding in nitride passivated Al interconnects** *5th International Workshop on Stress Induced Phenomena in Metallization*
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  Yu, C. L., Flinn, P. A., Bravman, J. C.
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